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Transistors Panasonic

2SC1384

Silicon NPN epitaxial planar type

For low-frequency power amplification and driver amplification Complementary to 2SA0684

■ Features

- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Complementary pair with 2SA0684

\blacksquare Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	60	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Emitter-base voltage (Collector open)	V _{EBO}	5	V	
Collector current	I_{C}	1	A	
Peak collector current	I_{CP}	1.5	A	
Collector power dissipation	P _C	1	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C ,	

■ Package

- Code
 - TO-92L-A1
- Pin Name
 - 1. Emitter
 - 2. Collector
 - 3. Base

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

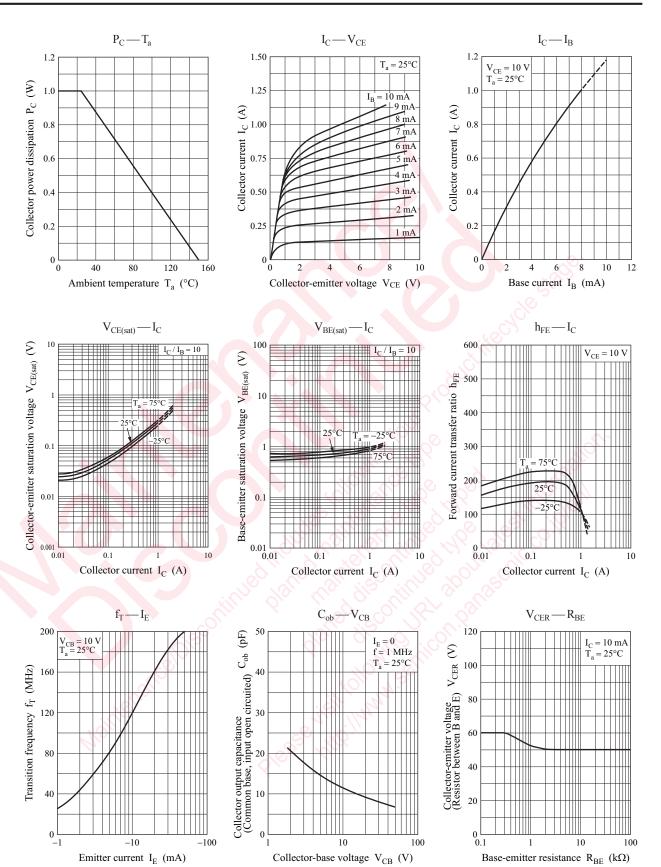
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	60	10		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50	O _L		V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 10 \mu A, I_C = 0$	5	,		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = 20 \text{ V}, I_{\rm E} = 0$	60		0.1	μA
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	85		340	
	h _{FE2}	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	50			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.20	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C _{re}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		11	20	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement
 - *2: Rank classification

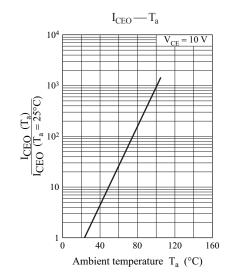
Rank	Q	R	S
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340

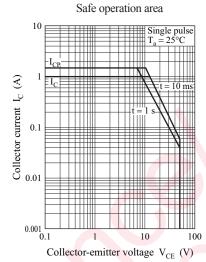
2SC1384 Panasonic



2 SJC00421AED

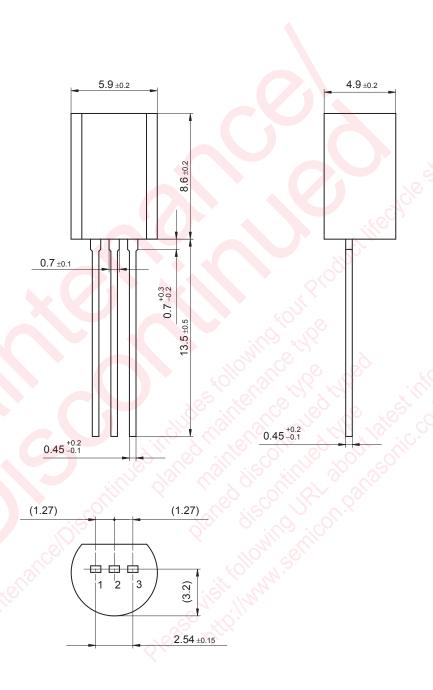
Panasonic 2SC1384





SJC00421AED 3

TO-92L-A1 Unit: mm



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